

2N5770

NPN SILICON PLANAR EPITAXIAL TRANSISTOR

2N5770 is NPN silicon planar epitaxial transistor designed for small signal high frequency amplifiers and oscillators.

CASE TO-92A



EBC

ABSOLUTE MAXIMUM RATINGS

Collector-Base Voltage	VCBO	30V
Collector-Emitter Voltage	VCEO	15V
Emitter-Base Voltage	VEBO	2V
Collector Current	IC	50mA
Total Power Dissipation @ TA=25°C	Ptot	625mW
@ TA=65°C		300mW
@ TC=25°C		1W
Operating Junction & Storage Temperature	Tj, Tstg	-55 to +150°C

ELECTRICAL CHARACTERISTICS AT (TA=25°C unless otherwise noted)

PARAMETER	SYMBOL	MIN	MAX	UNIT	TEST CONDITIONS
Collector-Base Breakdown Voltage	BVCBO	30		V	IC=100µA IE=0
Collector-Emitter Breakdown Voltage	BVCEO	15		V	IC=3mA IB=0
Emitter-Base Breakdown Voltage	BVEBO	3		V	IE=10µA IC=0
Collector Cutoff Current	ICBO		10 1	nA µA	VCB=15V IE=0 VCB=15V TA=150°C
Collector-Emitter Saturation Voltage	VCE(SAT)		0.4	V	IC=10mA IB=1mA
Base-Emitter Saturation Voltage	VBE(SAT)		1	V	IC=10mA IB=1mA
Current Gain-Bandwidth Product	fT	800 typ.		MHz	IC=8mA VCE=10V
Output Capacitance	Cob		1.7	pF	VCB=10V IE=0
Input Capacitance	Cib		2	pF	VEB=0.5V IC=0
Noise Figure	NF		6	dB	IC=1mA VCE=6V RG=400Ω f=60MHz

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